

Silicon NPN Power Transistor

2SD1545

DESCRIPTION

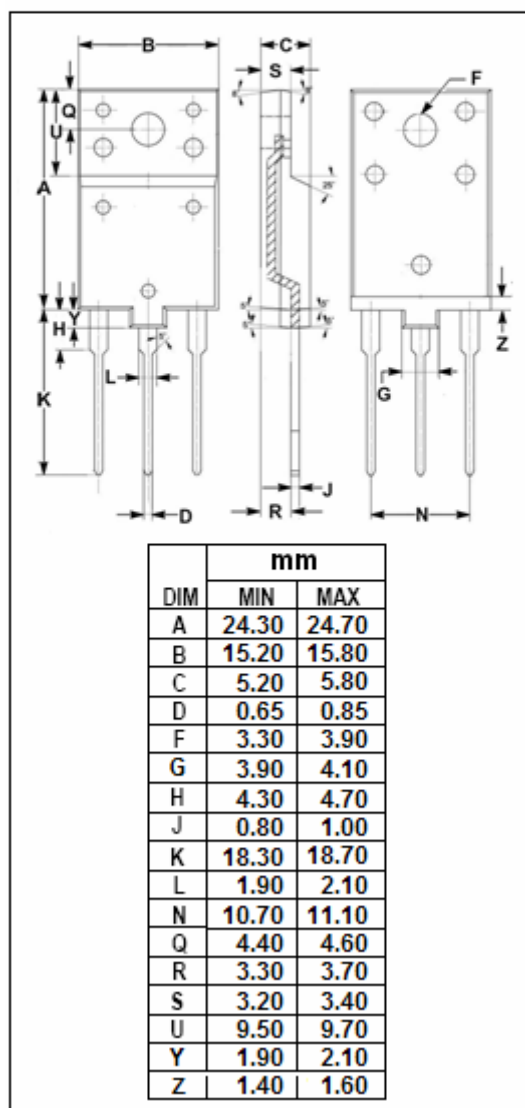
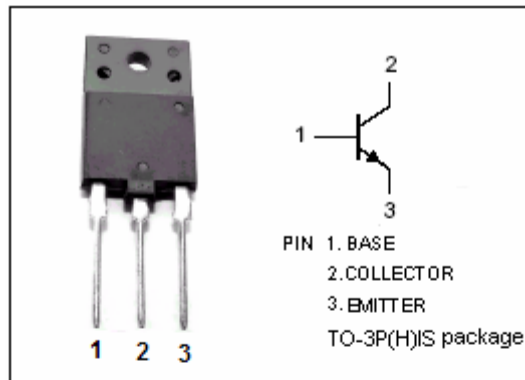
- High Breakdown Voltage-
: $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- Low Saturation Voltage

APPLICATIONS

- Color TV horizontal output applications
- Switching regulator output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	5	A
I_B	Base Current- Continuous	2.5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4.0A; I _B = 0.8A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4.0A; I _B = 0.8A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 500V ; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V ; I _C = 0			1.0	mA
h _{FE}	DC Current Gain	I _C = 1A ; V _{CE} = 5V	8			
f _T	Current-Gain—Bandwidth Product	I _C = 0.1A ; V _{CE} = 10V		3		MHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} = 1.0MHz		165		pF
t _f	Fall Time	I _{CP} = 4A , I _{B1(end)} = 0.8A		0.5	1.0	μ s

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